N-Channel 40-V (D-S) MOSFET

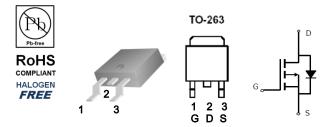
Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

Typical Applications:

- AEC-Q101 qualified and PPAP capable
- · Load Switches
- DC/DC Conversion CircuitsIndustrial
- Motor Drives

PRODUCT SUMMARY				
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I□ (A)		
40	1.55 @ V _{GS} = 10V	400 ^a		
	$1.9 @ V_{GS} = 4.5V$	400		



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Limit	Units				
Drain-Source Voltage	V_{DS}	40	V				
Gate-Source Voltage	V_{GS}	±20	V				
Continuous Drain Current a	T _C =25°C	I _D	400	А			
Pulsed Drain Current ^b		I _{DM}	1200	Α			
Continuous Source Current (Diode Conduction) ^a T _C =25		I _S	400	Α			
Power Dissipation ^a	T _C =25°C	P_{D}	300	W			
Operating Junction and Storage Temperature Range	· ·	T_J,T_stg	-55 to 175	°C			

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Maximum	Units
Maximum Junction-to-Ambient °	$R_{\theta JA}$	62.5	°C/W
Maximum Junction-to-Case	$R_{\theta JC}$	0.5	C/VV

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Notes

- a. Package Limited
- b. Pulse width limited by maximum junction temperature
- c. Surface Mounted on 1" x 1" FR4 Board.

Electrical Characteristics

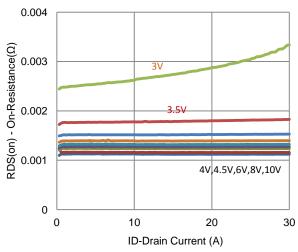
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit		
Static								
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \text{ uA}$	1			V		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA		
Zero Gate Voltage Drain Current	,	$V_{DS} = 32 \text{ V}, V_{GS} = 0 \text{ V}$			1 uA			
Zero Gate Voltage Brain Gurrent	I _{DSS}	$V_{DS} = 32 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10	uA		
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	150			Α		
Drain-Source On-Resistance ^a	r	$V_{GS} = 10 \text{ V}, I_{D} = 45 \text{ A}$			1.55	mΩ		
Drain-Source On-Resistance	r _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 44 \text{ A}$			1.9	11122		
Forward Transconductance ^a	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 30 \text{ A}$		117		S		
Diode Forward Voltage ^a	V_{SD}	$I_S = 200 \text{ A}, V_{GS} = 0 \text{ V}$		1.2		V		
		Dynamic ^b						
Total Gate Charge	Q_g	$V_{DS} = 20 \text{ V}, V_{GS} = 4.5 \text{ V},$		118				
Gate-Source Charge	Q_{gs}	$I_{DS} = 20 \text{ V}, V_{GS} = 4.3 \text{ V},$ $I_{D} = 2 \text{ A}$		32		nC		
Gate-Drain Charge	Q_gd	10 - 2 A		39				
Turn-On Delay Time	t _{d(on)}	$V_{DS} = 20 \text{ V}, R_1 = 10 \Omega,$		34				
Rise Time	t _r	$V_{DS} = 20 \text{ V}, R_L - 10 \Omega,$ $I_D = 2 \text{ A},$		48		ns		
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		349				
Fall Time	t _f	V GEN = 10 V, 1 (GEN = 0.12		132				
Input Capacitance	C _{iss}			12409				
Output Capacitance	C _{oss}	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		1223		pF		
Reverse Transfer Capacitance	C_{rss}			483				

Notes

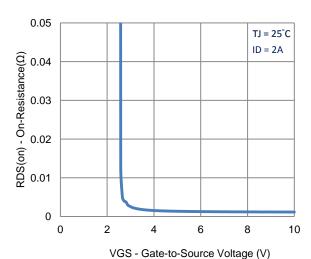
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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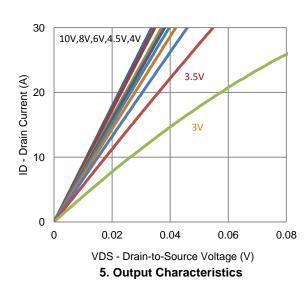
Typical Electrical Characteristics



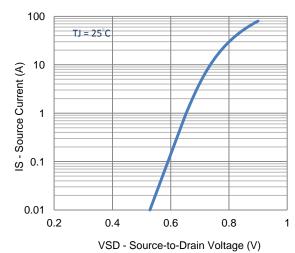
1. On-Resistance vs. Drain Current



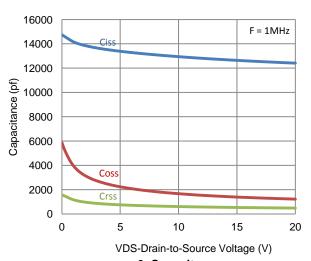
3. On-Resistance vs. Gate-to-Source Voltage



2. Transfer Characteristics

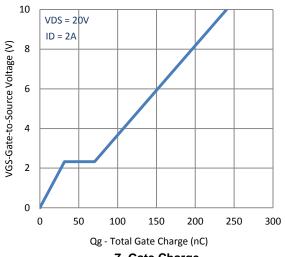


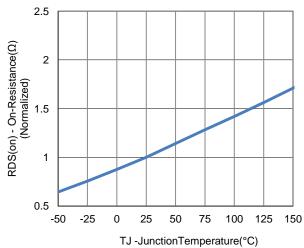
4. Drain-to-Source Forward Voltage



6. Capacitance

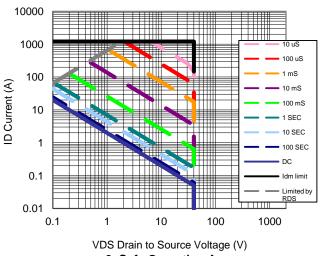
Typical Electrical Characteristics

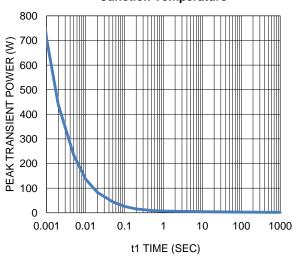




7. Gate Charge

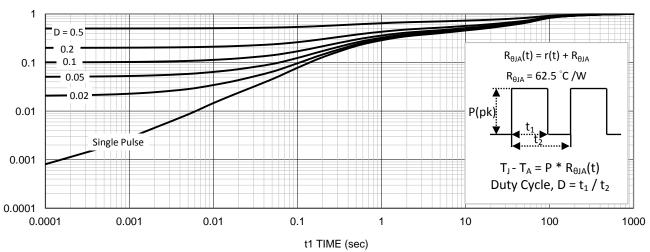






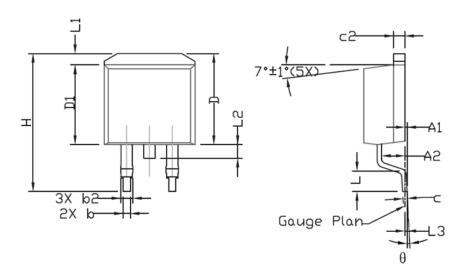
9. Safe Operating Area

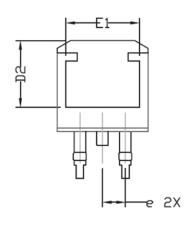
10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Package Information





CVMDEI	DIMENS:	IONAL F	REQMTS	INCH	INCHES REQMTS		
SYMBOL	MIN	NDM	MAX	MIN	NDM	MAX	
A	4,30	4.57	4,72	0.169	0.180	0,186	
A1	0		0,25	0		0.010	
A2	2,47	2.57	2,67	0.097	0.101	0,105	
b	0.69	0,813	0.94	0.027	0.032	0.037	
b2	1.17	1.27	1,45	0.046	0.050	0.057	
_	0.48	0,50	0,60	0.019	0.020	0.024	
c2	1,17	1.27	1.37	0.046	0.050	0,054	
D	9,80	10.05	10.30	0.386	0,396	0.406	
D1	8,64	8.78	9,65	0,340	0,346	0,380	
D2	7.12	7.37	7,62	0.280	0.290	0,300	
E	9,70	10.15	10.54	0,382	0.400	0.415	
E1	8,00	8,20	8,40	0,315	0,323	0.331	
е	2,54 BSC			0.100 BSC			
H	14,99	15,24	15,49	0.590	0.600	0.610	
L	1,78	2.29	2.79	0.070	0.090	0.110	
L1	1.02	1.27	1.52	0.040	0,050	0,060	
L2			1.75			0.069	
L3		0,254			0.010		
θ	0.		8.	0°		8°	